



Abstract

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For the correction of anamorphism in the case of a projection lens of an EUV projection exposure apparatus for wafers it is proposed to tilt the reticle bearing the
5 pattern to be projected and preferably also the wafer by a small angle about an axis that is perpendicular to the axis A of the lens and perpendicular to the scan direction and that in each instance passes through the middle of the light field generated on the reticle or on the wafer. For
10 the correction of a substantially antisymmetric quadratic distortion the reticle and/or the substrate is instead rotated about an axis of rotation that is disposed at least approximately parallel to an optical axis of the projection lens.